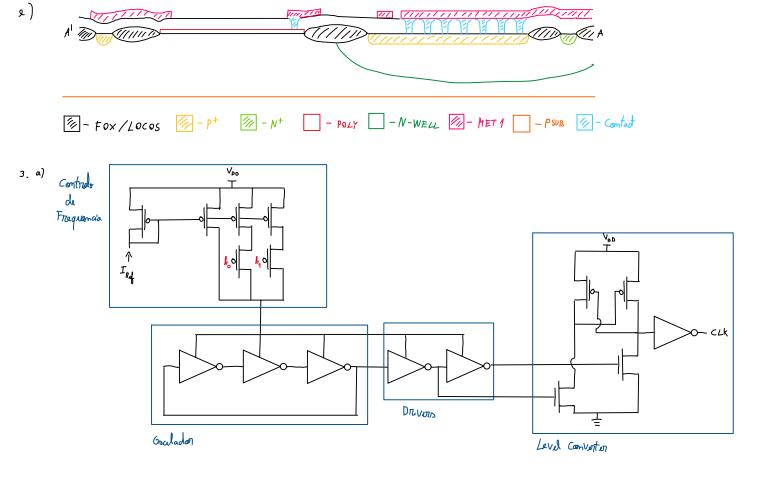


O efeito de corpo é o aumento da tensão de *threshold* com o aumento da tensão da *source* para o *bulk*. Este efeito dá-se nos transístores indicados.

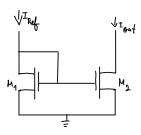


(4 Transistors no saturação > Von=200mV

$$I_{D} = \frac{\mu_{C_{OX}}}{2} \cdot \frac{W}{L} \cdot V_{OD}^{2} \implies I_{Out} = \frac{\left(\frac{W}{L}\right)_{H_{1}}}{\left(\frac{W}{L}\right)_{M}} I_{DU}$$

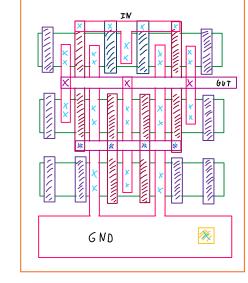
$$\left(\frac{w}{L}\right)_{H_1} = 4\left(\frac{w}{L}\right)_{H_1}$$

$$\left(\frac{W}{L}\right)_{M_A} = \frac{2 \cdot T_{RA}}{\mu_{C_{QX}}} \cdot \frac{1}{V_{QQ}^2} = 0.295 \implies \left(\frac{W}{L}\right)_{M_A} = 1.176$$



Panu aplican common contraid

Ngation M = 2



- Durmmy Gates My Gates MET 1
- // M2 Gates ____ Met 2

- P SUB

- 4) a) Este circuito permite escolher entre uma fonte de corrente NMOS ou PMOS com um bit.
 - M1 M3 M5: Espelho NMOS
 - M2 M4: Espelho PMOS
 - M6 M7: Switches que permitem comutar entre as fontes.
 - H My-M2-M3-M4-M5: Saturação -> 5 VOD = 200 mV

$$i = c \frac{\partial V}{\partial t} \iff \frac{\mu c_{0x}}{2} \cdot \frac{W}{L} \cdot V_{00}^{2} = c \frac{\partial V}{\partial t} \iff \frac{W}{L} = \frac{2c}{\mu c_{0x}} \cdot \frac{1}{V_{00}^{2}} \cdot \frac{\partial V}{\partial t}$$

Pasa Mag My:

$$\left(\frac{W}{L}\right)_{ij} = \sqrt{\left(\frac{W}{L}\right)_{ij}}$$

$$\left(\frac{w}{L}\right)_{H_{4}} = \omega \left(\frac{w}{L}\right)_{H_{L}} \qquad \left(\frac{w}{L}\right)_{H_{5}} = \beta \left(\frac{w}{L}\right)_{H_{3}} = \overline{\sigma}\left(\frac{w}{L}\right)_{H_{4}}$$

M6-M7: Switches - Dimensões munimus

- -L=0.35 Nm
- -W = Q 4 pm